### FAIRCHILD

SEMICONDUCTOR

### KSC3552

# High Voltage and High Reliabilty High Speed Switching

- Wide SOA



1.Base 2.Collector 3.Emitter

### **NPN Silicon Transistor**

Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

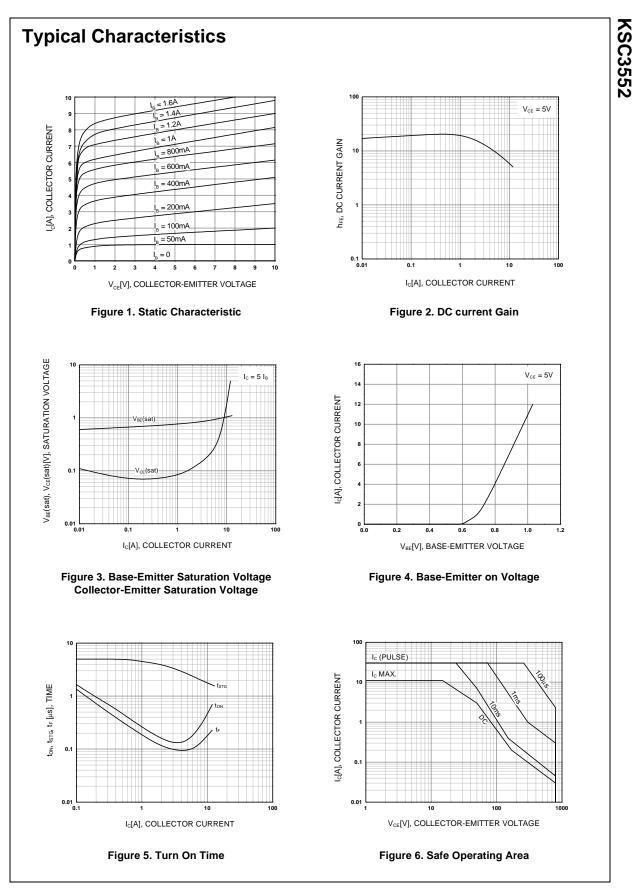
Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	1100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	12	A
I <sub>CP</sub>	Collector Current (Pulse)	30	A
I <sub>B</sub>	Base Current	6	A
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	150	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics ${\tt T_C=25^{\circ}C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>E</sub> = 0	1100			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0	800			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 6A, I <sub>B1</sub> = -I <sub>B2</sub> = 1.2A L = 500μH, Clamped	800			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 800V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.8A$	10		40	
h <sub>FE2</sub>		$V_{CE} = 5V, I_{C} = 4A$	8			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A, I <sub>B</sub> = 1.2A			2	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A, I <sub>B</sub> = 1.2A			1.5	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 1MHz		215		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.8A		15		MHz
t <sub>ON</sub>	Turn ON Time	V <sub>CC</sub> = 400V			0.5	μs
t <sub>STG</sub>	Storage Time	$51_{B1} = -2.5I_{B2} = I_C = 8A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 50\Omega$			0.3	μs

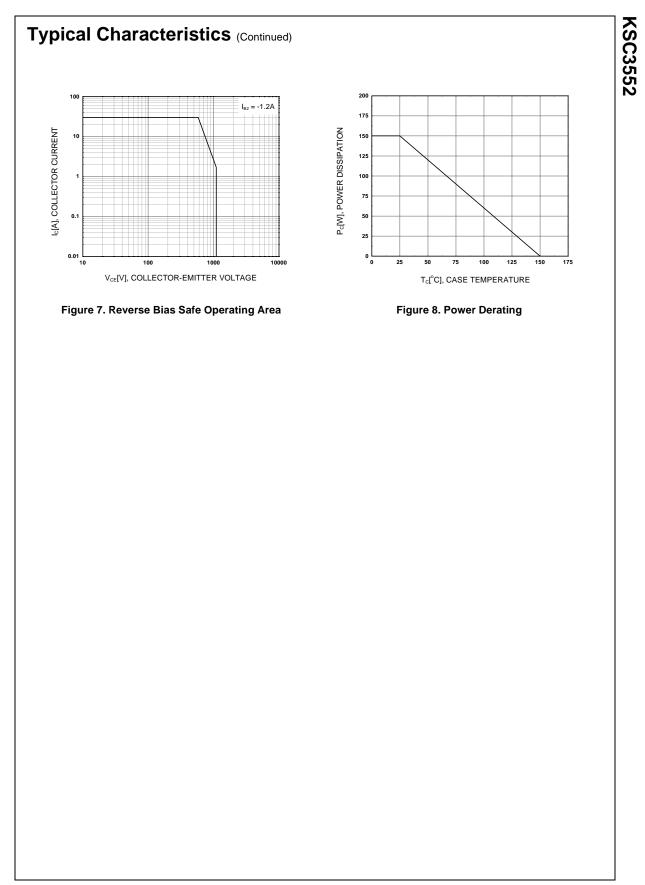
### h<sub>FE</sub> Classificntion

Classification	Ν	R	0
h <sub>FE</sub>	10 ~ 20	15 ~ 30	20 ~ 40

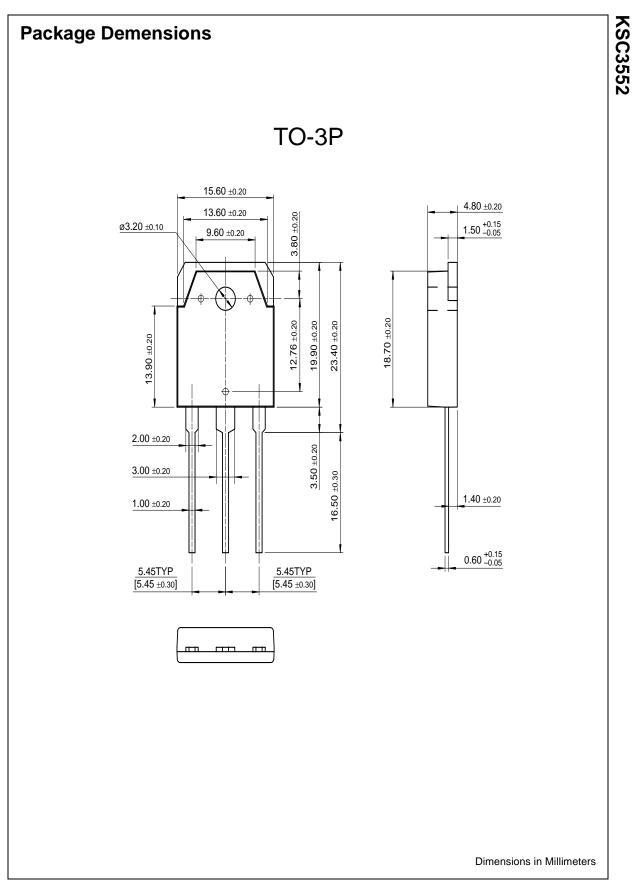


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Rev. A1, June 2001



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